

NXH80B120H2Q0

Power Integrated Module, Dual Boost, 1200 V, 40 A IGBT + 1200 V, 15 A SiC Diode

The NXH80B120H2Q0SG is a power integrated module (PIM) containing a dual boost stage consisting of two 40A/1200V IGBTs, two 15A/1200V SiC diodes, and two 25A/1600V anti-parallel diodes for the IGBTs. Two additional 25A/1600V bypass rectifiers used for inrush current limit are included. An on-board thermistor is included.

- IGBT Specifications: $V_{CE(SAT)} = 2.2\text{ V}$, $ESW = 2180\text{ }\mu\text{J}$
- 25 A / 1600 V Bypass and Anti-parallel Diodes
- SiC Rectifier Specification: $V_F = 1.4\text{ V}$
- Solderable Pins
- Dual Boost 40 A / 1200 V IGBT + SiC Rectifier Hybrid Module
- Thermistor
- Fast IGBT with low $V_{CE(SAT)}$ for high efficiency
- Low V_F bypass diodes for excellent efficiency in bypass mode
- SiC Diode for high speed switching
- Easy mounting
- Solar Inverter Boost Stage
- Solar Inverter
- UPS